

# COMPUTER DIODE

200mA

Low Power, Switching

JAN, JANTX & JANTXV 1N3600

JAN, JANTX & JANTXV 1N4150

JAN, JANTX & JANTXV 1N4150-1

## FEATURES

- Metallurgical Bond
- Qualified to MIL-S-19500/231
- Planar Passivated Chip
- DO-7 or DO-35 Package
- Non-JAN Available

## DESCRIPTION

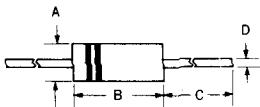
This series of switching diodes is useful in many computer switching applications, for both military and commercial systems.

### ABSOLUTE MAXIMUM RATINGS, AT 25°C

Reverse Breakdown Voltage	75V
Peak Working Voltage	50V
Average Output Current	200mA
Surge Current (1sec) (1 $\mu$ sec)	0.5A 4.0A
Operating Temperature Range	-65°C to +175°C
Storage Temperature Range	-65°C to +200°C

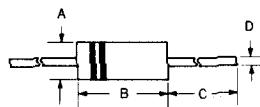
### MECHANICAL SPECIFICATIONS

J, JTX & JTXV 1N3600

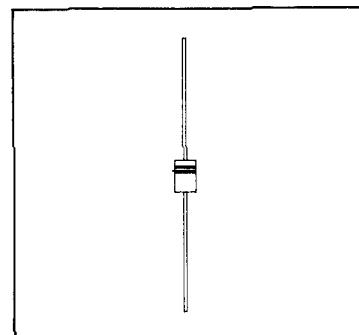


	INCHES	MILLIMETERS
A	.078 - .107	1.98 - 2.72
B	.195 - .300	4.95 - 7.62
C	1.0 MIN.	25.40 MIN.
D	.018 - .022	.46 - .56

J, JTX & JTXV 1N4150, 1N4150-1



	INCHES	MILLIMETERS
A	.056 - .075	1.42 - 1.90
B	.140 - .180	3.55 - 4.57
C	1.0 MIN.	25.40 MIN.
D	.018 - .022	.46 - .56



## ELECTRICAL SPECIFICATIONS (at 25°C unless noted)

Characteristics	Forward Voltage	Forward Voltage	Forward Voltage	Forward Voltage	Forward Voltage	Reverse Breakdown Voltage
Conditions	$V_{F1}$ $I_F = 1 \text{ mA DC}$	$V_{F2}$ $I_F = 10 \text{ mA DC}$	$V_{F3}$ $I_F = 50 \text{ mA DC (pulse)}$	$V_{F4}$ $I_F = 100 \text{ mA DC (pulse)}$	$V_{F5}$ $I_F = 200 \text{ mA DC (pulse)}$	$BV$ $I_R = 5.0 \mu\text{A DC}$
Minimum Maximum	0.540 Vdc 0.620 Vdc	0.660 Vdc 0.740 Vdc	0.760 Vdc 0.860 Vdc	0.820 Vdc 0.920 Vdc	0.870 Vdc 1.00 Vdc	75 Vdc —

Characteristics	Reverse Current	Reverse Current	Junction Capacitance	Reverse Recovery Time	Reverse Recovery Time	Forward Recovery Time
Conditions	$I_R$ $V_R = 50 \text{ VDC}$	$I_R$ $V_R = 50 \text{ VDC}$ $T_A = 150^\circ\text{C}$	$C$ $V_R = 0$ $F = 1 \text{ MHz}$ $V_{sig} = 50 \text{ mv (p-p)}$	$t_{rr1}$ $I_F = I_R = 10 \text{ to } 200 \text{ mA DC}$ $R_L = 100 \text{ ohms}$	$t_{rr2}$ $I_F = I_R = 200 \text{ to } 400 \text{ mA DC}$ $R_L = 100 \text{ ohms}$	$t_{fr}$ $I_F = 200 \text{ mA DC}$ $t_p = 100 \text{ nsec}$ $t_r = 0.4 \text{ nsec}$
Maximum	0.1 $\mu\text{A DC}$	100 $\mu\text{A DC}$	2.5 pf	4 nsec	6 nsec	10 nsec

